

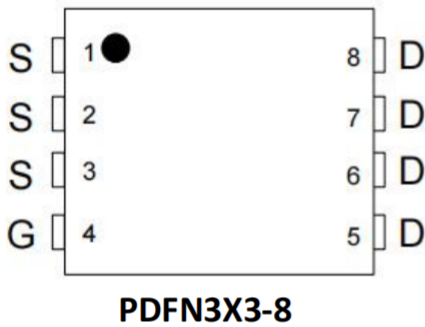
**Product Summary**

- $V_{DS}$  -150 V
- $I_{DS}$  -9.0A
- $R_{DS(ON)}$  (at  $V_{GS}=-10V$ ) <296mΩ

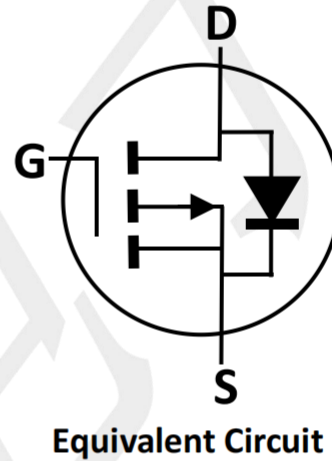
**Application**

- Load switch
- Portable equipment and battery Powered systems
- Active Clamp in Intermediate DC/DC Power Supplies

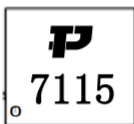
**Package and Pin Configuration**



**Circuit diagram**



**Marking**



**Absolute Maximum Ratings (T<sub>A</sub>=25°C unless otherwise noted)**

| PARAMETER                      | SYMBOL     | LIMIT             | UNIT |
|--------------------------------|------------|-------------------|------|
| Drain-Source Voltage           | $V_{DS}$   | -150              | V    |
| Gate-Source Voltage            | $V_{GS}$   | ±20               | V    |
| Continuous Drain Current       | $I_D$      | $T_C=25^\circ C$  | -9   |
|                                |            | $T_C=125^\circ C$ | -4   |
| Pulsed Drain Current           | $I_{DM}$   | -15               | A    |
| Total Power Dissipation        | $P_{DTOT}$ | 52                | W    |
| Operating Junction Temperature | $T_J$      | 150               | °C   |
| Storage Temperature Range      | $T_{stg}$  | -55 to +150       | °C   |

**Thermal Characteristic**

| PARAMETER                              | Symbol     | Value | Unit |
|----------------------------------------|------------|-------|------|
| Junction-to-Ambient Thermal Resistance | $R_{thJA}$ | 81    | °C/W |

Note : When mounted on 1" square PCB (FR4 material).

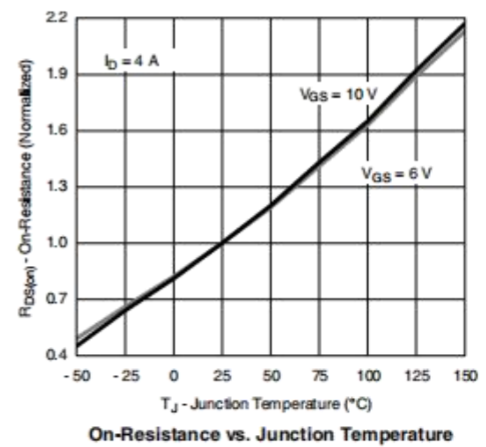
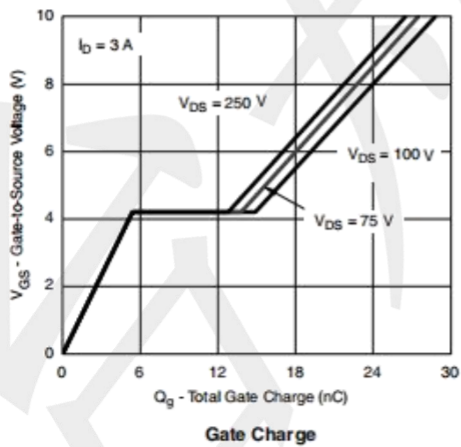
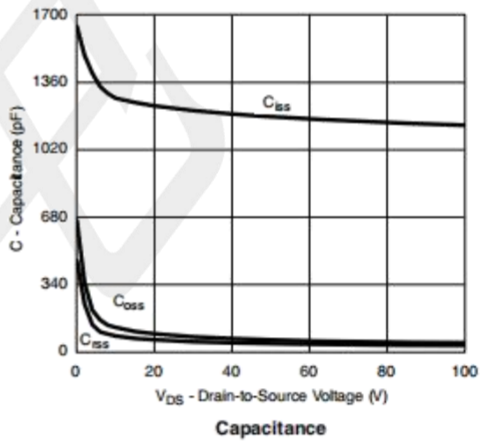
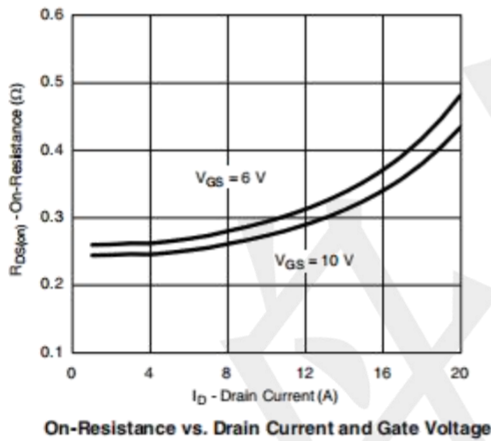
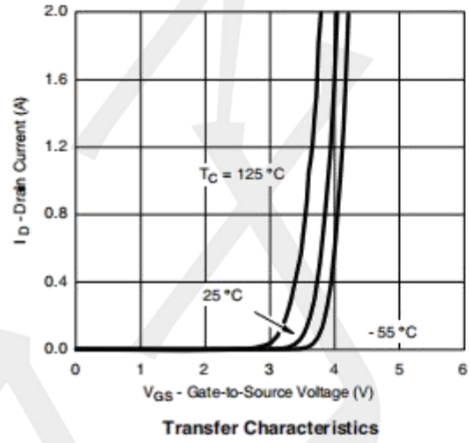
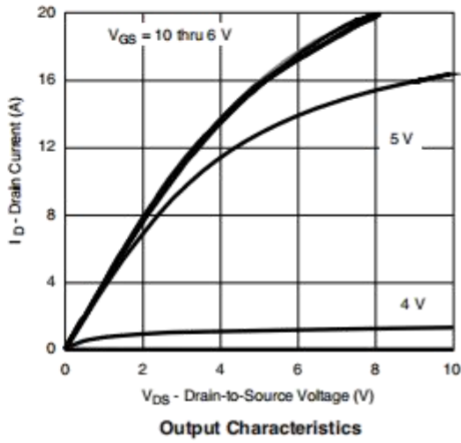
**Electrical Characteristics (T<sub>A</sub>=25°C unless otherwise noted)**

| PARAMETER                                                      | CONDITIONS                                                                                        | SYMBOL              | MIN  | TYP  | MAX  | UNIT |
|----------------------------------------------------------------|---------------------------------------------------------------------------------------------------|---------------------|------|------|------|------|
| <b>Static</b>                                                  |                                                                                                   |                     |      |      |      |      |
| Drain-Source Breakdown Voltage                                 | V <sub>GS</sub> =0V, I <sub>D</sub> =-250μA                                                       | BV <sub>DSS</sub>   | -150 | --   | --   | V    |
| Gate-Source Threshold Voltage                                  | V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> = -250μA                                        | V <sub>GS(th)</sub> | -2   | -3   | -4   | V    |
| Gate-Source Leakage                                            | V <sub>DS</sub> =0V, V <sub>GS</sub> = ±20V                                                       | I <sub>GSS</sub>    | --   | --   | ±100 | nA   |
| Zero Gate Voltage Drain Current                                | V <sub>DS</sub> = -120V, V <sub>GS</sub> =0V                                                      | I <sub>DSS</sub>    | --   | --   | -1   | μA   |
|                                                                | V <sub>DS</sub> = -120V, T <sub>J</sub> =55°C                                                     |                     | --   | --   | -10  | μA   |
| Drain-Source On-State Resistance<br>(Note 1)                   | V <sub>GS</sub> = -10V, I <sub>D</sub> = -1A                                                      | R <sub>DS(on)</sub> | --   | 242  | 296  | mΩ   |
|                                                                | V <sub>GS</sub> = -10V, T <sub>J</sub> = 125°C                                                    |                     | --   | 420  | --   |      |
|                                                                | V <sub>GS</sub> = -6V, I <sub>D</sub> = -3A                                                       |                     | --   | 261  | 316  |      |
| Forward Transconductance (Note 2)                              | V <sub>DS</sub> = -15V, I <sub>D</sub> = -4A                                                      | g <sub>fs</sub>     | --   | 12   | --   | S    |
| <b>Dynamic (Note 2)</b>                                        |                                                                                                   |                     |      |      |      |      |
| Total Gate Charge (Note 3)                                     | V <sub>DS</sub> = -75V, I <sub>D</sub> = -3A,<br>V <sub>GS</sub> = -6V                            | Q <sub>g</sub>      | --   | 23.2 | 35   | nC   |
| Gate-Source Charge (Note 3)                                    |                                                                                                   | Q <sub>gs</sub>     | --   | 5.4  | --   |      |
| Gate-Drain Charge (Note 3)                                     |                                                                                                   | Q <sub>gd</sub>     | --   | 8.4  | --   |      |
| Input Capacitance                                              | V <sub>DS</sub> = -50V, V <sub>GS</sub> = 0V,<br>F = 1.0MHz                                       | C <sub>iss</sub>    | --   | 1190 | --   | pF   |
| Output Capacitance                                             |                                                                                                   | C <sub>oss</sub>    | --   | 61   | --   |      |
| Reverse Transfer Capacitance                                   |                                                                                                   | C <sub>rss</sub>    | --   | 42   | --   |      |
| <b>Switching</b>                                               |                                                                                                   |                     |      |      |      |      |
| Turn-On Delay Time (Note 3)                                    | V <sub>DD</sub> = -75V, I <sub>D</sub> = -3A,<br>V <sub>GS</sub> = -10V,<br>R <sub>GEN</sub> = 1Ω | t <sub>d(on)</sub>  | --   | 11   | 18   | nS   |
| Rise Time (Note 3)                                             |                                                                                                   | t <sub>r</sub>      | --   | 28   | 42   |      |
| Turn-Off Delay Time (Note 3)                                   |                                                                                                   | t <sub>d(off)</sub> | --   | 52   | 78   |      |
| Fall Time (Note 3)                                             |                                                                                                   | t <sub>f</sub>      | --   | 35   | 53   |      |
| <b>Source-Drain Diode Ratings and Characteristics (Note 2)</b> |                                                                                                   |                     |      |      |      |      |
| Forward Voltage                                                | V <sub>GS</sub> = 0V, I <sub>F</sub> = -3A                                                        | V <sub>SD</sub>     | --   | -0.8 | -1.2 | V    |
| Continuous Source Current                                      | Integral reverse diode<br>in the MOSFET                                                           | I <sub>S</sub>      | --   | --   | -9   | A    |
| Pulsed Current (Note 1)                                        |                                                                                                   | I <sub>SM</sub>     | --   | --   | -15  | A    |

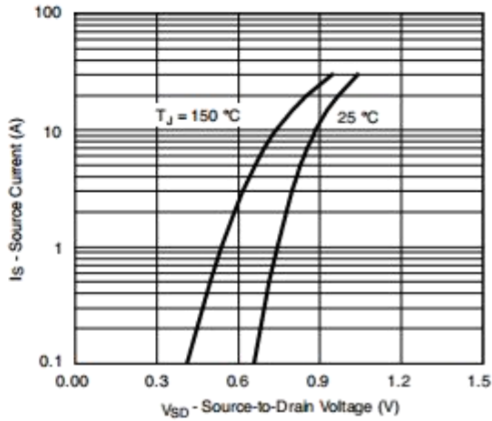
Notes:

1. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2%.
2. Guaranteed by design, not subject to production testing.
3. Independent of operating temperature

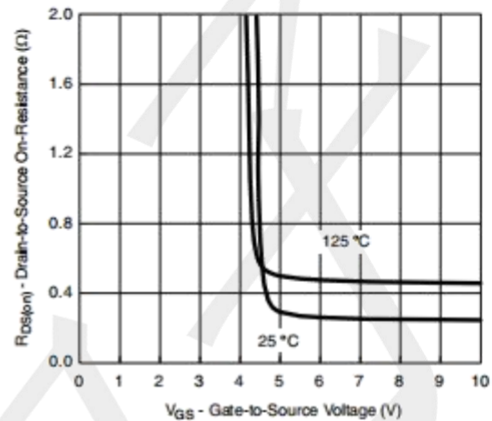
**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



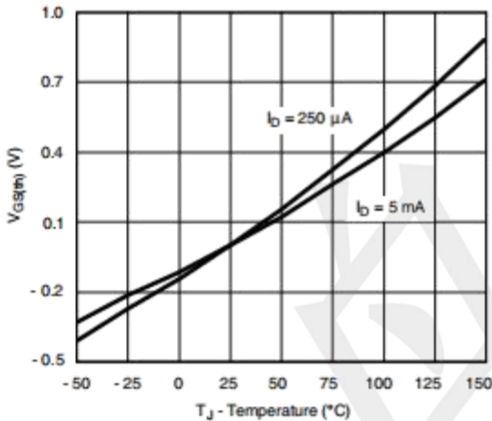
## TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



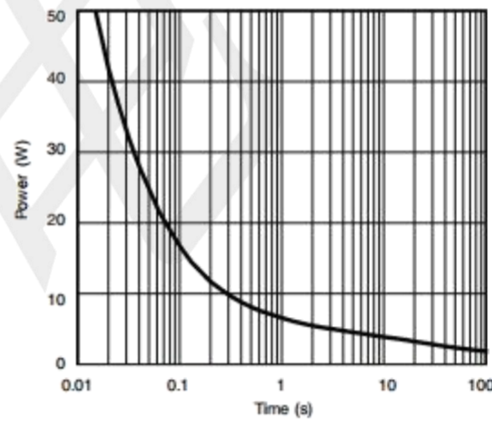
Source-Drain Diode Forward Voltage



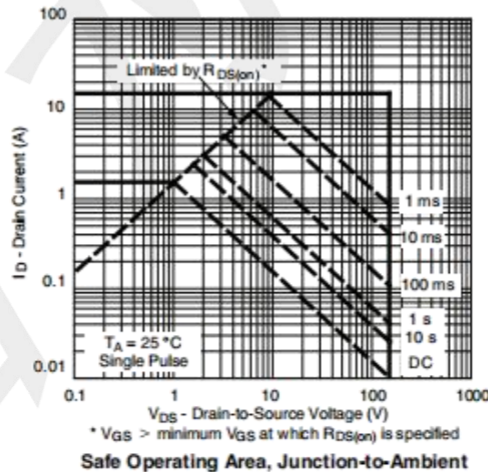
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage

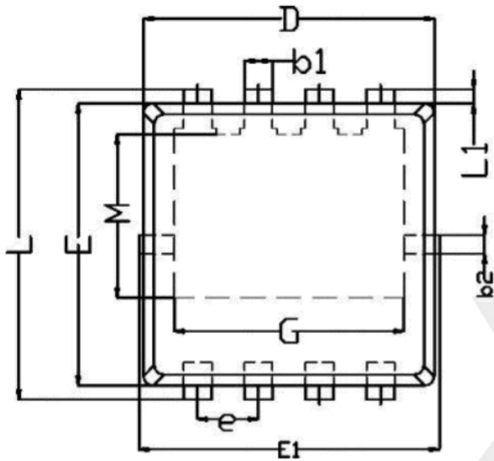


Single Pulse Power, Junction-to-Ambient

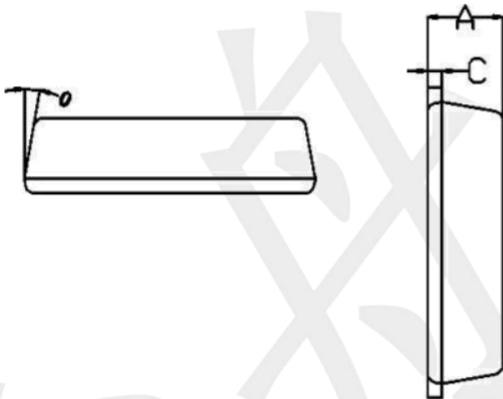


\* The power dissipation PD is based on  $T_J(\text{max}) = 150^\circ\text{C}$ , using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

**PDFN3X3-8 Package Information**



| Syabol | Din in mi |       |       |
|--------|-----------|-------|-------|
|        | Min       | Nom   | Max   |
| A      | 0.75      | 0.80  | 0.85  |
| L1     | 0.10      | 0.15  | 0.20  |
| b1     | 0.25      | 0.30  | 0.35  |
| b2     | 0.15      | 0.20  | 0.25  |
| C      | 0.10      | 0.15  | 0.20  |
| D      | 3.050     | 3.100 | 3.150 |
| e      | 0.650OSO  |       |       |
| E      | 2.950     | 3.000 | 3.050 |
| E1     | 3.150     | 3.200 | 3.250 |
| L      | 3.250     | 3.300 | 3.350 |
| M      | 1.685     | 1.735 | 1.785 |
| G      | 2.400     | 2.450 | 2.500 |
| 0      | 0"        | 5,    | w     |



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